

Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0172	SERIAL NUMBER 10/754814 <i>Not Assigned</i>
	APPLICANT KAMIYAMA et al.	
	FILING DATE 01/12/2004 Concurrently Herewith	GROUP 2807

U.S. Patent Documents

Foreign Patent Documents

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

TL	Manzur Gill, Tyler Lowrey and John Park, "Ovonic Unified Memory – A High-Performance Nonvolatile Memory Technology for Stand-Alone Memory and Embedded Applications", 2002 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, 3 pages
TL	A. Pirovano, A.L. Lacaita, D. Merlani, A. Benvenuti, F. Pellizzer and R. Bez, "Electronic Switching Effect in Phase-Change Memory Cells", 2002 IEEE International Electron Devices Meeting, Technical Digest, pp. 923-926
TL	Y.N. Hwang et al., "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors", 2003 Non-Volatile Semiconductor Memory Workshop, Digest of Technical Papers, pp. 91-92
EXAMINER	<i>Thoyle</i>
	DATE CONSIDERED
	<i>6/18/05</i>

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*This abstract corresponds to Japanese Patent 3127220 above

**The English abstract of this document is Japanese Publication 10-246764 above

PTO1449